IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Yong-Bae Kim and Philippe)	
Schoenborn)	
Filed: Herewith)	
)	Group Art Unit: Unknown
Serial Number: Unknown)	-
)	Examiner: Unknown
Title: "Process for Removal of Photoresist Mask Used)	
for Making Vias in Low K Carbon-Doped)	
Silicon Oxide Dielectric Material, and for)	
Removal of Etch Residues from Formation of)	
Vias and Removal of Photoresist Mask")	

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.56

Honorable Commissioner for Patents Post Office Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR 1.56, 1.97, and 1.98, Applicants submit the attached form PTO-1449 (modified). This application is a continuation application of Serial No. 09/898,194. Since all of the documents listed on the enclosed form PTO-1449 (modified) were previously cited to or by the USPTO in the prior application, under the provisions of 37 C.F.R. 1.98(d), copies of the listed documents are not enclosed.

Respectfully submitted,

John P. Taylor

Attorney for Applicants Registration No. 22,369

Date: July 14, 2003

(909) 699-7551

Mailing Address:

Sandeep Jaggi, Chief Intellectual Property Counsel Intellectual Property Law Department LSI Logic Corporation 1551 McCarthy Blvd., Mail Stop D-106 Milpitas, CA 95035

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FORM PTO-1449 (Modified) U.S. Department of Commerce, Patent and Trademark Office						Docket No. Serial No. 01-125/1C					
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			Մ.	S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclas	ss	Filing Da If Appropria			
	AA	5,874,367	2/23/99	Dobson	438	787		787			
	AB	6,028,015	2/22/00	Wang et al.	438	789		3/29/99			
	AC	6,114,259	9/5/00	Sukharev et al.	438	789		7/27/99			
	AD	6,147,012	11/14/00	Sukharev et al.	438	787		11/12/99			
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	AF	6,232,658	5/15/01	Catabay et al.	257	701		6/30/99			
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AR	Bothra, S., et al., "Integration of 0.25 µm Three and Five Level Interconnect System for High Performance ASIC", 1997 Proceedings Fourteenth International VMIC Conference, Santa Clara, CA, June 10-12, 1997, pp.43-48.
AS	Dobson, C.D., et al., "Advanced SiO $_2$ Planarization Using Silane and H_2O_2 ", Semiconductor International, December 1994, pp. 85-88.
 AT	McClatchie, S., et al., "Low Dielectric Constant Oxide Films Deposited Using CVD Techniques", 1998 Proceedings Fourth International DUMIC Conference, February 16-17, 1998, pp. 311-318.

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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	вв	6,417,080	7/2002	Yokoshima	438	514					
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	BE	6,030,901	2/2000	Hopper et al.	204	192.36					
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

Sheet of <u>5</u> sheets FORM PTO-1449 (Modified) Docket No. Serial No. U.S. Department of Commerce, Patent and Trademark Office 01-125/1C INFORMATION DISCLOSURE STATEMENT BY APPLICANT Applicants Yong-Bae Kim et al. (Use several sheets if necessary) Filing Date Group Herewith Unknown U.S. Patent Documents *Examiner Document Filing Date Initial Number Date Name Class Subclass Appropriate CA 5,904,154 5/18/99 Chien et al. 134 1.2 7/24/97 CB 5,882,489 3/16/99 Bersin et al. 204 192.35 4/26/96 CC 5,858,879 1/12/99 Chao et al. 725 438 6/6/97 CD 3,012,861 12/12/61 Ling 23 223.5 1/15/60 CE 3,178,392 4/13/65 Kriner 260 46.5 4/9/62 CF 3,832,202 8/27/74 Ritchie 106 287 8/8/72 CG 3,920,865 11/18/75 Läufer et al. 427 220 4/6/72 CH 4,705,725 11/10/87 Glajch et al. 428 405 11/28/86

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CR CS CT

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FORM PTO-1449 (Modified)
U.S. Department of Commerce, Patent and Trademark Office

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

Yong-Bae Kim et al.

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	DB	6,051,477	4/18/00	Nam	438	404	10/22/96		
	DC	6,025,263	2/15/00	Tsai et al.	438	624	9/11/97		
	DD	5,939,763	8/17/99	Hao et al.	257	411	9/5/96		
	DE	5,864,172	1/26/99	Kapoor et al.	257	634	8/13/96		
	DF	5,688,724	11/18/97	Yoon et al.	437	235	12/23/94		
	DG	5,470,801	11/28/95	Kapoor et al.	437	238	6/28/93		
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	DI	4,771,328	9/13/88	Malaviya et al.	357	49	11/24/86		
	DJ	3,652,331	3/28/72	Yamazaki	117	201	3/13/69		
	DK					<u> </u>	<u> </u>		
			Fore	eign Patent Documents					
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	DP	<u> </u>		<u> </u>				<u> </u>	
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	DS	Silica Film	ns for Inter	al., "Chemical Vapor rlayer Dielectric App , <u>Electrochemical Soc</u>	lication"	, 1999 Joi	nt		
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	EA	5,628,871	5/13/97	Shinagawa	438	514		6/24/94
	EB	6,153,524	11/28/00	Henley et al.	438	691 7/28/9		7/28/98
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	EE	5,558,718	9/24/96	Leung	118	723E		4/8/94
	EF	6,037,248	3/14/00	Ahn	438	619		6/13/97
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